

ABSTRACT

An etching apparatus includes: a processing container configured to be evacuated to form a vacuum atmosphere in the processing container and including a wall that has an alloy composed of aluminum and an additive metal as a base material; a stage installed in the processing container and configured to mount a substrate having a metal film formed on a surface of the substrate; a gas supplier installed in the processing container and configured to supply an oxidizing gas that oxidizes the metal film and an etching gas that is β -diketone to the stage to etch the oxidized metal film; and a wall heater configured to heat the wall to a temperature in a range of 60 degrees C to 90 degrees C when the etching gas is supplied from the gas supplier into the processing container.

(FIG. 1)